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## In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently amended) A field effect transistor comprising

a conduction channel of sub-lithographic a first
width,

source and drain regions located at opposite ends of said conduction channel, said source and drain regions having silicide sidewalls on a surface thereof, and

polysilicon gate regions on opposing sides of said conduction channel and recessed from said source and drain regions, said polysilicon gate regions having silicide sidewalls formed thereon, wherein the smallest feature of said field effect transistor formed through a lithographic process is of a second width, wherein said first width is smaller than said second width and wherein said first width is defined as sub-lithographic.

2. (Original) A field effect transistor as recited in claim 1, wherein said silicide sidewalls are in the form of a liner.

- 3. (Original) A field effect transistor as recited in claim 1, wherein said polysilicon regions are connected by a connector.
- 4. (Original) A field effect transistor as recited in claim 3, wherein said connector is a damascene connector.
- 5. (Currently amended) A field effect transistor as recited in claim 4, wherein said damascene conductor

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<u>connector</u> is formed in a trench in at least one of an isolation structure or a pad material extending over an edge of said polysilicon gate regions.

- 6. (Original) A field effect transistor as recited in claim 1, wherein said silicide sidewalls are connected by a connector.
- 7. (Currently amended) A field effect resistor transistor as recited in claim 6, wherein said connector is a Damascene damascene connector.
- 8. (Currently amended) A field effect transistor as recited in claim 7, wherein said damascene conductor connector is formed in a trench in at least one of an isolation structure or a pad material extending over an edge of said polysilicon gate regions.
- 9. (Canceled)
- 10. (Canceled)
- 11. (Canceled)
- 12. (Canceled)
- 13. (Canceled)
- 14. (Canceled)
- 15. (Canceled)
- 16. (Canceled)
- 17. (Canceled)